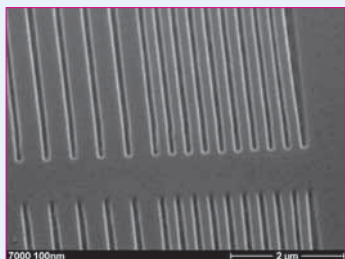
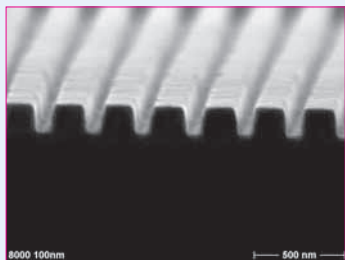


Thermoplastic Polymers for Nanoimprint Lithography

mr-I 7000E, mr-I 8000E — Thermoplastics with Improved Imprinting Behaviour



100 nm trenches, pitch 300 and 500 nm,
 Film thickness: 200 nm
 Imprint: 130 °C, 3 min, 50 bar
 Complete filling of stamp cavities
 Residual layer thickness < 10 nm



100 nm trenches, pitch 300 nm,
 Film thickness: 200 nm
 Imprint: 190 °C, 3 min, 50 bar
 Complete filling of stamp cavities
 Residual layer thickness < 10 nm

Unique features

- Excellent film quality
- Plasma etch resistance superior to PMMA
- Attainable smallest feature size at least 50 nm (depending on stamp resolution)
- Safe solvents

Imprint conditions

mr-I 7000E

- T_g 60 °C
- Imprint temperatures 125 - 150 °C
- Imprint pressure 20 - 50 bar
- Etch selectivity to SiO₂ about 2 (CHF₃ plasma)
- Ready-to-use solutions for 100 nm, 200 nm, 300 nm film thickness (3000 rpm)

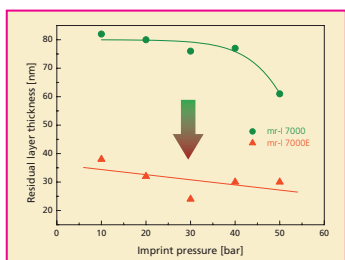
Imprint characteristics superior to mr-I 7000 and mr-I 8000 polymers

- ✓ Lower imprint pressure
- ✓ Lower residual layer thickness
- ✓ Shorter cycle times due to faster imprint

mr-I 8000E

- T_g 115 °C
- Imprint temperatures 170 - 190 °C
- Imprint pressure 20 - 50 bar
- Etch selectivity to SiO₂ about 2 (CHF₃ plasma)
- Ready-to-use solutions for 100 nm, 200 nm, 300 nm film thickness (3000 rpm)

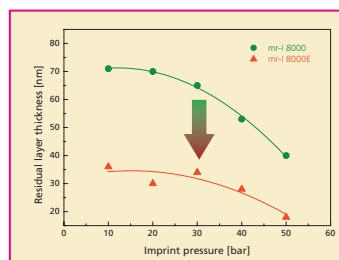
Lower residual layer thickness under gentle imprint conditions



Residual layer thickness as a function of imprint pressure

Film thickness: 200 nm
 Imprint: 10 s @ 100 °C
 Incomplete filling of stamp cavities

mr-I 7000 vs. mr-I 7000E

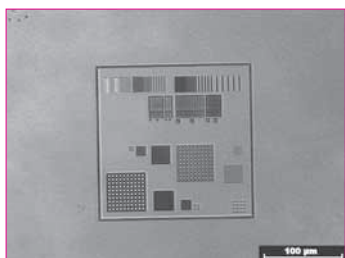


Residual layer thickness as a function of imprint pressure

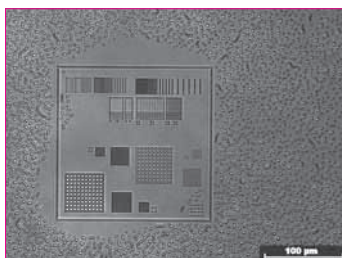
Film thickness: 200 nm
 Imprint: 10 s @ 160 °C
 Incomplete filling of stamp cavities

mr-I 8000 vs. mr-I 8000E

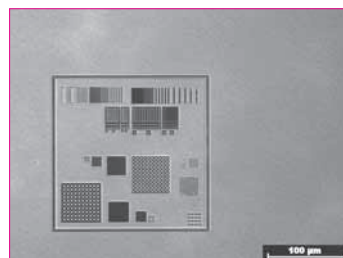
Defect-free imprints at lower pressure



mr-I 7000
 130 °C, 3 min,
50 bar
 no defects



mr-I 7000
 130 °C, 3 min,
20 bar
 insufficient polymer flow



mr-I 7000E
 130 °C, 3 min,
20 bar
 no defects